

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

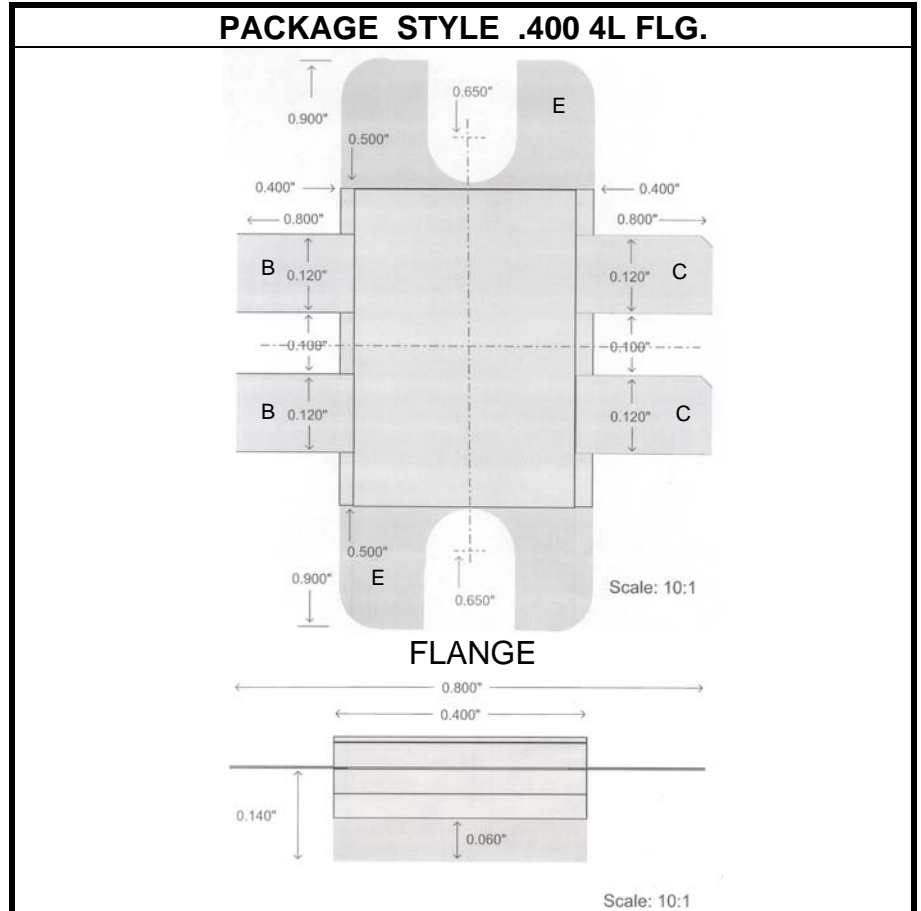
The **ASI MRA0510-50H** is Designed for Class AB Linear Amplifier Applications up to 1000 MHz.

FEATURES:

- **Omnigold™** Metalization System
- Diffused Ballast Resistors.
- Internal Matching Network

MAXIMUM RATINGS

V_{CEO}	30 V
V_{CBO}	60 V
V_{EBO}	4.0 V
P_{DISS}	125 W @ $T_C = 25\text{ }^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.4 °C/W


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 25\text{ mA}$	60			V
BV_{CBO}	$I_C = 25\text{ mA}$	60			V
BV_{EBO}	$I_E = 5.0\text{ mA}$	4.0			V
I_{CBO}	$V_{CB} = 30\text{ V}$			25	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	20		80	---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			24	pF
G_{PB} $VSRW$	$V_{CE} = 28\text{ V}$ $P_{out} = 50\text{ W}$ $I_{CQ} = 2 \times 120\text{ mA}$ $f = 1.0\text{ GHz}$	7.0 5:1			dB ---